

200mΩ Power Distribution Switches

Features

- 200mΩ Typ. High-Side MOSFET
- > 0.8A Current Limit (V_{IN}=3.0V)
- \triangleright Wide Input Voltage Range: 2V \sim 5.5V
- Soft Start
- Thermal Protection
- Small SOT-23-5 Package Minimizes Board Space

Applications

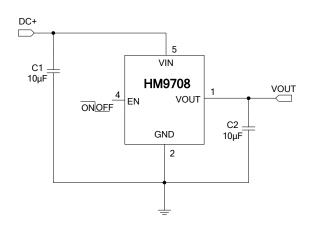
- > Battery-Powered Equipment
- Motherboard USB Power Switch
- > USB Device Power Switch
- Hot-Plug Power Supplies
- Battery-Charger Circuits

Description

The PT JÏ € is an integrated 200mΩ power switch for self-powered and bus-powered Universal Series Bus (USB) applications. Its low quiescent supply current (50μA) and small package (SOT-23-5) is particularly suitable in battery-powered portable equipment.

Several protection functions include soft start to limit inrush current during plug-in, current limiting at $0.8A(V_{IN}=3.0V)$ and thermal shutdown to protect damage under over current conditions.

Typical Application Circuit





Pin Assignment

TOP VIEW	Number	Name	Function		
	1	VOUT	Output Pin		
	2	GND	Ground		
	3	NC	No Used		
1 2 3	4	EN	ON/OFF Control (High Enable)		
SOT-23-5L	5	VIN	Power Input		

Absolute Maximum Ratings (Note 1)

➤ Supply Voltage	7V
➤ Chip Enable	0.3V \sim 7V
➤ Power Dissipation, PD @ TA = 25°C	SOT-23-5 0.25W
➤ Operating Temperature Range	40°C ∼ +85°C
> Storage Temperature Range	65°C ∼ +150°C
> Junction Temperature	40°C ∼ +125°C
> Lead Temperature	+265℃

Note 1: Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.



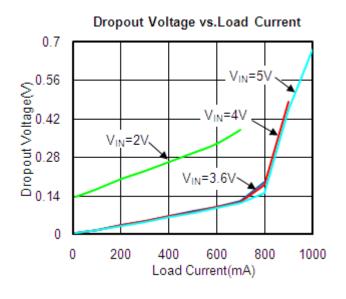
Electrical Characteristics

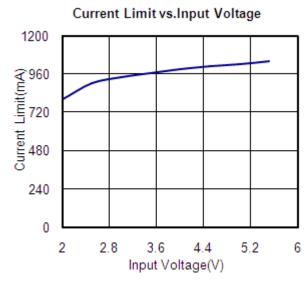
Operating Conditions: TA = 25 $^{\circ}$ C, V_{IN} = 5V, C_{IN} = C_{OUT} = 10 μ F, unless otherwise specified.

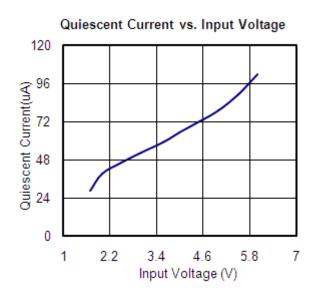
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IN}	Input Voltage Range		2		5.5	V
R _{DS(ON)}	Output NMOFET R _{DS(ON)}	V _{IN} =5.0V,I _{LOAD} =500 mA	100	200	250	mΩ
ΙQ	Supply Current	V _{IN} =3.0V		50		μA
	Зирріу Сипені	V _{IN} =5.0V	40	80	160	μA
I _{LIMIT}	Current Limit Threshold	V _{IN} =3.0V		800		mA
V _{ENH}	EN Input High Threshold		1.5			V
V _{ENL}	EN Input Low Threshold				0.6	V
I _{OFF}	Shutdown Supply Current	V _{EN} = 0V		0.5	1	μA
V _{UVLO}	VIN Under Voltage Lockout	I _{OUT} =300mA, V _{IN} : 2.4V→0V		1.7		V
$\Delta V_{ m UVLO}$	VIN Under Voltage Hysterics			150		mV
T _{SD}	Thermal Limit			130		$^{\circ}$
ΔT_{SD}	Thermal Limit Hysterics			20		$^{\circ}$

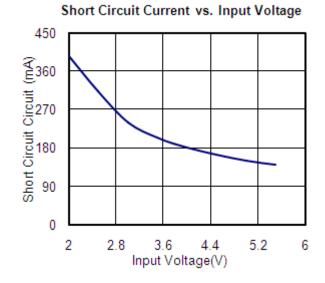


Typical Operating Characteristics





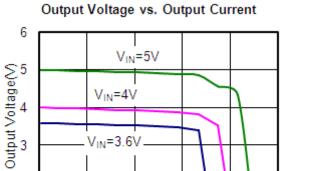


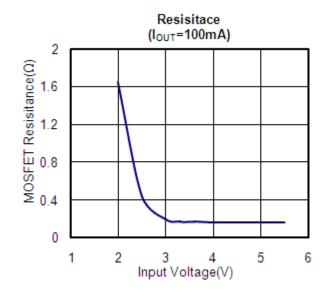






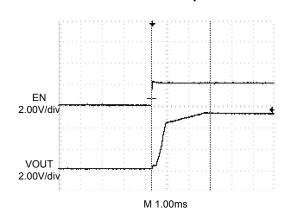
V_{IN}=2V



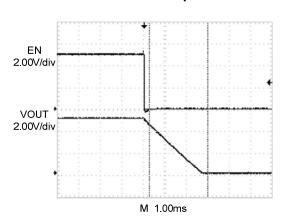


EN Turn-On Response

Output Current(mA)



EN Turn-Off Response





Pin Description

VOUT (Pin 1): Ideal Diode Cathode and Output. Bypass VOUT with ESR capacitor. However stability improves with higher ESRs.

GND (Pin 2): Power and Signal Ground for the IC.

NC (Pin 3): No used.

EN (Pin 4): Status Condition Indicator. This pin indicates the conducting status of the PT JÏ $\stackrel{\frown}{=}$. If the part is forward biased ($V_{IN} > V_{OUT} + V_{FWD}$) this pin will be Hi-Z. If the part is reverse biased ($V_{OUT} > V_{IN} + V_{RTO}$), then this pin will pull down 10mA through an open-drain. When terminated to a high voltage through a 470k resistor, a high voltage indicates diode conducting. May be left floating or grounded when not in use.

VIN (Pin 5): Ideal Diode Anode and Positive Power Supply for PT JÏ € . When operating PT JÏ € as a switch it must be bypassed with a low ESR ceramic capacitor.

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Application Information

The PT JÏ € is a high-side single switch with active-high enable input.

Input and Output

VIN (input) is the power supply connection to the circuitry and the drain of the output MOSFET. VOUT (output) is the source of the output MOSFET. In a typical circuit, current flows through the switch from VIN to VOUT toward the load. Both VOUT pins must be short on the board and connected to the load and so do both VIN pins but connected to the power source.

Thermal Shutdown

Thermal shutdown shuts off the output MOSFET if the die temperature exceeds 130° C and 20° C of hysterics forces the switch turning off until the die temperature drops to 110° C.

Filtering

To limit the input voltage drop during hot-plug events connect a $10\mu F$ ceramic capacitor from V_{IN} to GND. However, higher capacitor values will further reduce the voltage drop at the input.

Connect a sufficient capacitor from V_{OUT} to GND. This capacitor helps to prevent inductive parasitics from pulling V_{OUT} negative during turn-off or EMI damage to other components during the hot detachment. It is also necessary for meeting the USB specification during hot plug-in operation. If

HT $J\ddot{i}$ is implanted in device end application, minimum $1\mu F$ capacitor from V_{OUT} to GND is recommended and higher capacitor values are also preferred.

In choosing these capacitors, special attention must be paid to the Effective Series Resistance, ESR, of the capacitors to minimize the IR drop across the capacitor's ESR. A lower ESR on this capacitor can get a lower IR drop during the operation.

Ferrite beads in series with all power and ground lines are recommended to eliminate or significantly reduce EMI. In selecting a ferrite bead, the DC resistance of the wire used must be kept to a minimum to reduce the voltage drop.

Soft Start

In order to eliminate the upstream voltage droop caused by the large inrush current during hot-plug events, the "soft-start" feature effectively isolates power supplies from such highly capacitive loads.

Under-voltage Lockout

UVLO prevents the MOSFET switch from turning on until input voltage exceeds 1.7V (typical). If input voltage drops below 1.7V (typical), UVLO shuts off the MOSFET switch.

Current Limiting and Short Protection

The current limit circuit is designed to protect the system supply, the MOSFET switch and the load from damage caused by excessive currents. The current limit threshold is set internally to limit the output current to approximately0.8A typical(V_{IN} =3.0V). When the output is short to ground, it will limit to a constant current 30mA until thermal shutdown or short condition removed.



Reverse current preventing

The output MOSFET and driver circuitry are also designed to allow the MOSFET source to be externally forced to a higher voltage than the drain ($V_{OUT} > V_{IN} \ge 0$). To prevent reverse current from such condition, HT JÏ $\stackrel{?}{\in}$ will automatically shut off the MOSFET.

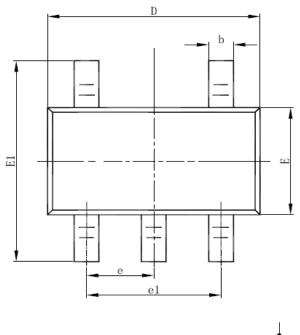
Layout and Thermal Dissipation

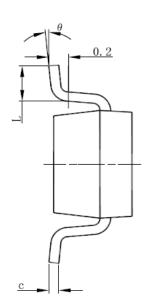
- 1. Place the switch as close to the USB connector as possible. Keep all traces as short as possible to reduce the effect of undesirable parasitic Inductance.
- 2. Place the output capacitor and ferrite beads as close to the USB connector as possible. If ferrite beads are used, use wires with minimum resistance and large solder pads to minimize connection resistance.
- 3. If ferrite beads are used, use wires with minimum resistance and large solder pads to minimize connection resistance.
- 4. If the package is with dual VOUT or VIN pins, short both the same function pins to reduce the internal turn-on resistance. If the output power will be delivered to two individual ports, it is especially necessary to short both VOUT pin at the switch output side in order to protect the switch when each port is plug-in separately.
- 5. Under normal operating conditions, the package can dissipate the channel heat away. Wide power bus planes connected to VIN and VOUT and a ground plane in contact with the device will help dissipate additional heat.

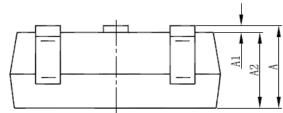


Package Information

SOT-23-5 Package Outline Dimension







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
Е	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	